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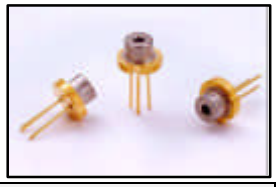
RLT8520MG TECHNICAL DATA

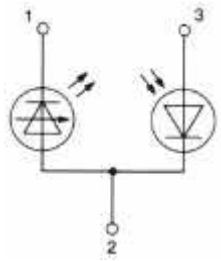


Infrared Laserdiode

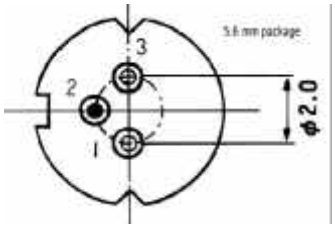
Structure: **AlGaAs double heterostructure**
Lasing wavelength: **850 nm typ.**
Max. optical power: **20 mW**
Package: **5.6 mm**

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laserdiode cathode
2) Laserdiode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	20	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operating Temperature	T_{op}	-10 .. +40	°C
Storage Temperature	T_{stg}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}	cw	8	10	12	mA
Operation Current	I_{op}	P_o = 20 mW	33	35	45	mA
Operation Voltage	V_{op}	P_o = 20 mW	1.8	1.9	2.1	V
Lasing Wavelength	λ_p	P_o = 20 mW	845	850	855	nm
Beam Divergence	$\theta_{//}$	P_o = 20 mW	8	10	11	°
Beam Divergence	$\theta_{\perp}$	P_o = 20 mW	25	30	40	°
Differential Efficiency	η	P_o = 20 mW	600	700	800	µW/mA
Monitor Current	I_m	P_o = 20 mW, V_r=5V	0.3	0.4	0.5	mA